## CLAIMIS

## What is claimed is:

- 1. A low dielectric material, comprising:
  - a polymer composition, wherein the polymer composition comprises at least one polymer component that further comprises at least one monomer component and wherein the at least one monomer component comprises a radical precursor chemically bonded to a structural precursor.
- 2. The low dielectric material of claim 1, wherein the radical precursor volatilizes during a cure process to form a plurality of ultranamopores and a gas.
- 3. The low dielectric material of claim 1, wherein the structural precursor forms a support material during a cure process.
- 4. The low dielectric material of claim 1, wherein the structural precursor comprises a siloxane compound.
- 5. The low dielectric material of claim 4, wherein the siloxane compound comprises an hydridosiloxane compound.
- 6. The low dielectric material of claim 4, wherein the siloxane compound comprises an organohydridosiloxane compound.
- 7. The low dielectric material of claim 1, wherein the structural pre-cursor comprises an organic compound.
- 8. The low dielectric material of claim 7, wherein the organic compound comprises a poly(arylene) ether compound.
- 9. The low dielectric material of claim 7, wherein the organic compound comprises a cage molecule.

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10. The low dielectric material of claim 9, wherein the cage molecule is an adamantanebased molecule.

- 11. The low dielectric material of claim 1, wherein the radical precursor comprises an alkyl group.
- 12. The low dielectric material of claim 11, wherein the alkyl group comprises at least one branched alkyl component.
- 13. The low dielectric material of claim 1, wherein the radical precursor comprises a cycloalkyl group.
  - 14. The low dielectric material of claim 1, wherein the radical precursor comprises an aromatic group.
  - 15. The low dielectric material of claim 1, wherein the radical precurror comprises at least one saturated bond.
  - 16. A low dielectric film comprising the low dielectric material of claim 1.
  - 17. An electronic component comprising the low dielectric material of claim 1.
  - 18. An electronic component comprising the low dielectric film of claim 16.
  - 19. A layered component comprising the low dielectric material of claim 1.
- 20. The low dielectric material of claim 1, wherein the material has a dielectric constant of less than about 3.
- 21. The low dielectric material of claim 20, wherein the material has a dielectric constant of less than about 2.5.
- 22. The low dielectric material of claim 21, wherein the material has a dielectric constant of less than about 2.
- 23. The low dielectric film of claim 16, wherein the film has a diel ectric constant of less than about 3.

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24. The low dielectric film of claim 23, wherein the film has a dielectric constant of less than about 2.5.

- 25. The low dielectric material of clairn 25, wherein the film has a dielectric constant of less than about 2.
- 26. The low dielectric material of claim 2, wherein the plurality of ultrananopores comprises at least two voids.
- 27. The low dielectric material of claim 26, wherein each of the at least two voids comprises a mean diameter of less than about 10 nanometers.
- 28. A method of forming a low dielectric material, comprising:
  - providing a polymer composition, wherein the polymer composition comprises at least one polymer component that further comprises at least one monomer component and wherein the at least one monomer component comprises a comprises a radical precursor chemically bonded to a structural precursor;
  - applying energy to the polymer composition, such that the radical precursor is volatilized; and
  - liberating at least in part the radical precursor from the polymer composition.
- 29. The method of claim 28, wherein forming the low dielectric rnaterial further comprises curing the polymer composition to form a support material and a plurality of pores.
- 30. The method of claim 29, wherein the plurality of pores comprise nanopores.
- 31. The method of claim 29, wherein the plurality of pores comprise ultrananopores.
- 32. The method of claim 28, wherein applying energy to the polymer composition comprises applying heat.
- 33. The method of claim 28, wherein the radical precursor comprises an alkyl group.

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34. The method of claim 33, wherein the alkyl group comprises at least one branched alkyl component.

- 35. The method of claim 28, wherein the structural precursor comprises a siloxane compound.
- 36. The method of claim 35, wherein the siloxane compound comprises an hydridosiloxane compound.
- 37. The method of claim 35, wherein the siloxane compound comprises an organohydridosiloxane compound.
- 38. The method of claim 28, wherein the structural precursor comprises an organic compound.
- 39. The method of claim 38, wherein the organic compound comprises a poly(arylen.e) ether compound.
- 40. The method of claim 38, wherein the organic compound comprises a cage mol ecule.
- 41. The method of claim 40, wherein the cage molecule is an adamantane-based molecule.